



DMN53D0U

#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C		
501/	2Ω @ V <sub>GS</sub> = 5V	300 mA		
50V	2.5Ω @ V <sub>GS</sub> = 2.5V	200 mA		

## **Features and Benefits**

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Mechanical Data**

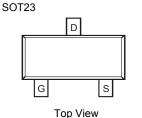
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (23)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

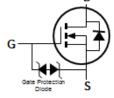






Top View





**Equivalent Circuit** 

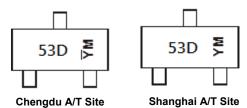
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0U-7	SOT23	3000/Tape & Reel
DMN53D0U-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



53D = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D	[	E	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage Continuous	V <sub>GSS</sub>	±12	V
Drain Current (Note 5) Continuous Pulsed	I <sub>D</sub> I <sub>DM</sub>	300 500	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

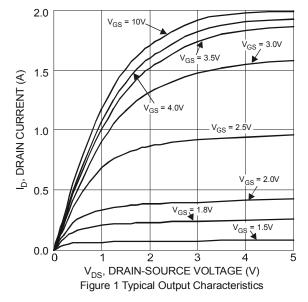
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	520	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	246	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

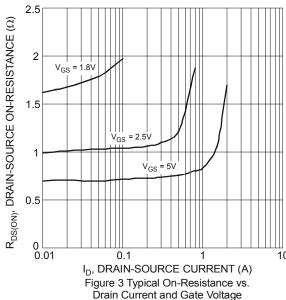
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

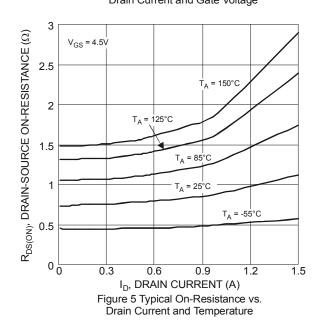
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μA	$V_{DS} = 50V, V_{GS} = 0V$		
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 6)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_ _ _		2.0 2.5 3.0	Ω	$V_{GS} = 5.0V, I_D = 50mA$ $V_{GS} = 2.5V, I_D = 50mA$ $V_{GS} = 1.8V, I_D = 50mA$		
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	_	_	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> =115mA		
DYNAMIC CHARACTERISTICS (Note 7)	<u> </u>			•		,		
Input Capacitance	C <sub>iss</sub>		37.1	_	pF	.,		
Output Capacitance	Coss	_	8.4	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>		4.0	_	pF	1.00012		
Total Gate Charge	$Q_g$	_	0.6	_	nC			
Gate-Source Charge	$Q_{gs}$		0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250\text{mA}$		
Gate-Drain Charge	$Q_{gd}$	_	0.1	_	nC			
Turn-On Delay Time	$t_{D(on)}$		2.1	_	ns			
Turn-On Rise Time	t <sub>r</sub>		2.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$		
Turn-Off Delay Time	$t_{D(off)}$		21	_	ns	$R_G = 25\Omega$ , $I_D = 200mA$		
Turn-Off Fall Time	t <sub>f</sub>		14	_	ns			

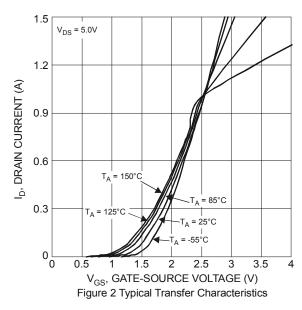
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
- Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

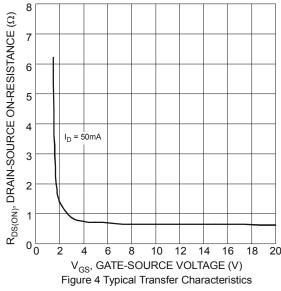












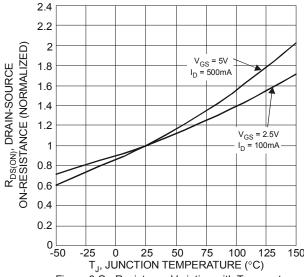
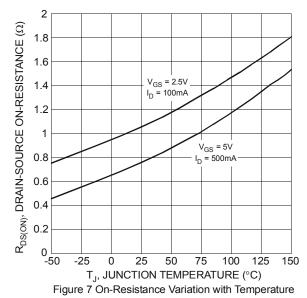
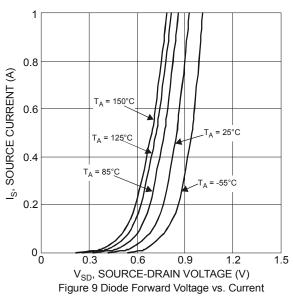
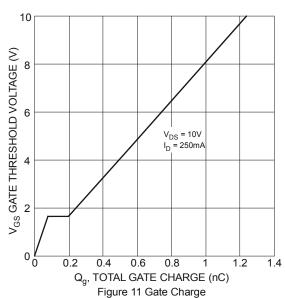


Figure 6 On-Resistance Variation with Temperature









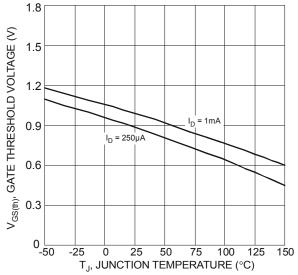
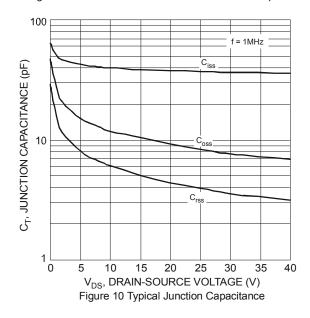


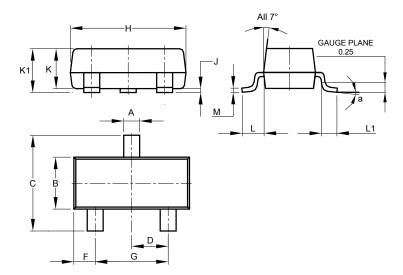
Figure 8 Gate Threshold Variation vs. Ambient Temperature





# **Package Outline Dimensions**

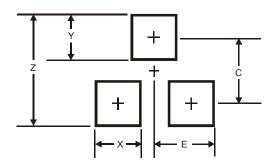
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Тур					
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
α	8°						
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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